

Customer No.: 31561  
Application No.: 10/708,372  
Docket No.: 12680-US-PA

#### AMENDMENTS TO CLAIMS

Please amend claims as follows.

Claims 1-11 (canceled).

12. (currently amended) A shallow trench isolation, comprising:

a substrate, having a trench therein;

an insulating layer, disposed in the trench, wherein the insulating layer has an upper surface higher than an upper surface of the substrate; and

a liner layer, formed over the substrate covering the insulating layer, wherein the liner layer is adopted for protecting the shallow trench isolation from external stress or thermal effect.

13. (original) The shallow trench isolation according to claim 12, wherein the liner layer further extends to an upper surface of the substrate.

14. (original) The shallow trench isolation according to claim 12, wherein the liner layer has a low etching selectivity relative to the insulating layer.

15. (original) The shallow trench isolation according to claim 12, wherein the liner layer has a thickness between 50 angstrom to 200 angstrom.

16. (original) The shallow trench isolation according to claim 12, wherein the liner layer comprises an insulating layer.

17. (original) The shallow trench isolation according to claim 16, wherein the liner layer is a silicon nitride layer.

18. (original) The shallow trench isolation according to claim 12, further comprising a pad oxide layer formed between the liner layer and the substrate.

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19. (original) The shallow trench isolation according to claim 12, further comprising another insulating layer covering the liner layer.
20. (new) A shallow trench isolation, comprising:  
a substrate, having a trench therein;  
an insulating layer, disposed in the trench, wherein the insulating layer has an upper surface higher than an upper surface of the substrate; and  
a liner layer, formed over the substrate covering the insulating layer, wherein the liner layer comprises a CVD silicon nitride layer.
21. (new) The shallow trench isolation according to claim 20, wherein the liner layer further extends to an upper surface of the substrate.
22. (new) The shallow trench isolation according to claim 20, wherein the liner layer has a low etching selectivity relative to the insulating layer.
23. (new) The shallow trench isolation according to claim 20, wherein the liner layer has a thickness between 50 angstrom to 200 angstrom.
24. (new) The shallow trench isolation according to claim 20, wherein the liner layer comprises an insulating layer.
25. (new) The shallow trench isolation according to claim 20, further comprising a pad oxide layer formed between the liner layer and the substrate.
26. (new) The shallow trench isolation according to claim 20, further comprising another insulating layer covering the liner layer.